

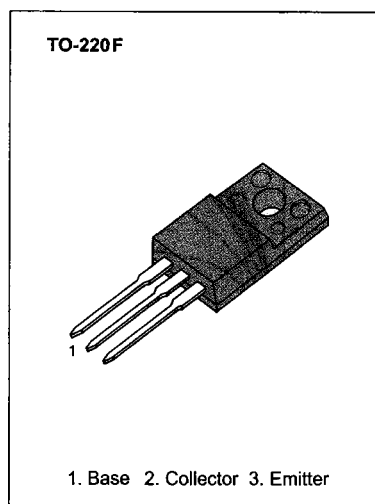
## PNP Transistor KSB1022 datasheet

### HIGH POWER SWITCHING APPLICATIONS

- High DC Current Gain
- Low Collector Emitter Saturation Voltage
- Complement to KSD1417

### ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Characteristic	Symbol	Rating	Unit
Collector Base Voltage	V <sub>CBO</sub>	-60	V
Collector Emitter Voltage	V <sub>CEO</sub>	-60	V
Emitter Base Voltage	V <sub>EBO</sub>	-5	V
Collector Current (DC)	I <sub>C</sub>	-7	A
Collector Current (Pulse)	I <sub>C</sub>	-10	A
Base Current	I <sub>B</sub>	-0.7	A
Collector Dissipation (Ta=25°C)	P <sub>C</sub>	2	W
Collector Dissipation (Tc=25°C)	P <sub>C</sub>	30	W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55~150	°C



### ELECTRICAL CHARACTERISTICS (Ta=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Emitter Breakdown Voltage	BV <sub>CEO</sub>	I <sub>C</sub> = -50mA, I <sub>B</sub> = 0	-60			V
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> = -60V, I <sub>E</sub> = 0			-100	μA
Emitter Cutoff Current	I <sub>EB0</sub>	V <sub>EB</sub> = -5V, I <sub>C</sub> = 0			-4	mA
DC Current Gain	h <sub>FE1</sub>	V <sub>CE</sub> = -3V, I <sub>C</sub> = -3A	2000		15000	
	h <sub>FE2</sub>	V <sub>CE</sub> = -3V, I <sub>C</sub> = -7A	1000			
Collector Emitter Saturation Voltage	V <sub>CE(sat)1</sub>	I <sub>C</sub> = -3A, I <sub>B</sub> = -6mA		-0.95	-1.5	V
	V <sub>CE(sat)2</sub>	I <sub>C</sub> = -7A, I <sub>B</sub> = -14mA		-1.3	-2	V
Base Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = -3A, I <sub>B</sub> = -6mA		-1.55	-2.5	V
Turn On Time	t <sub>on</sub>	-I <sub>B1</sub> = I <sub>B2</sub> = 6mA		0.8		μS
Storage Time	t <sub>sig</sub>	V <sub>CC</sub> = -45V		2		μS
Fall Time	t <sub>f</sub>			2.5		μS

# PNP Transistor KSB1022 datasheet

